21. An article comprising: a storage medium, said storage medium having instructions stored thereon, said instructions, when executed, resulting in the capability to design the layout of an integrated circuit chip for fabrication, the integrated circuit chip including a gate array architecture;

the gate array architecture including a semiconductor substrate having a plurality of N-type diffusion regions and P-type diffusion regions; said diffusion regions having partially overlying polysilicon landing sites, at least one forming both N-type and P-type transistors;

wherein the regions are relatively-sized to form two distinct transistor sizes, smaller N- and P-type transistors and larger N- and P-type transistors.

44. The integrated circuit of claim 1, wherein successive rows of small diffusion regions are followed by successive rows of regular-sized diffusion regions;

wherein immediately successive rows within similarly-sized diffusion regions have opposite polarity.